

# 電磁學 (一) Electromagnetics (I)

## 7. 電容

## Capacitance

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In this lecture, we will introduce a charge-storage device, called capacitor.

- 7.1 Charge storage 電荷儲存
- 7.2 Parallel-plate capacitor 平板電容器
- 7.3 Cylindrical and spherical capacitors 圓柱及球形電容器
- 7.4 Capacitor circuit 電容電路
- 7.5 Review 單元回顧

電容

Capacitance

7.1 電荷儲存

Charge Storage

## Observation 1

Faraday's law of electrostatics  $\nabla \times \vec{E} = 0$

➡  $\vec{E} \equiv -\nabla V$  defines electric potential

Gauss Law  $\nabla \cdot \vec{D} = \rho \Rightarrow \nabla \cdot \vec{E} = \frac{\rho}{\epsilon}$

➡  $-\nabla \cdot \nabla V = \frac{\rho}{\epsilon}$  or  $\nabla^2 V = -\frac{\rho}{\epsilon}$   
(Poisson's equation)

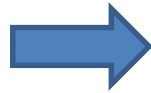
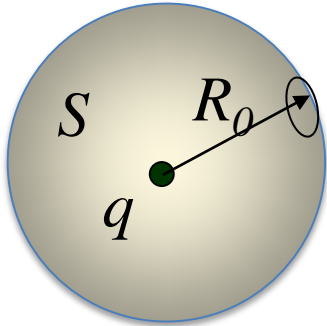
$V \propto \rho$  : electric potential  $V$  is linearly proportional to charge  $\rho$

## Observation 2

•  $q' = +1$

$$\vec{E} = E_R \hat{a}_R = \frac{q}{4\pi\epsilon_0 R^2} \hat{a}_R$$

$$V(R_0) = -\int_{\infty}^{R_0} \vec{E} \cdot \hat{a}_R dR = \frac{q}{4\pi\epsilon_0 R_0}$$



$$V \propto q$$

electric potential  $V$  is linearly proportional to charge  $q$

# Capacitance

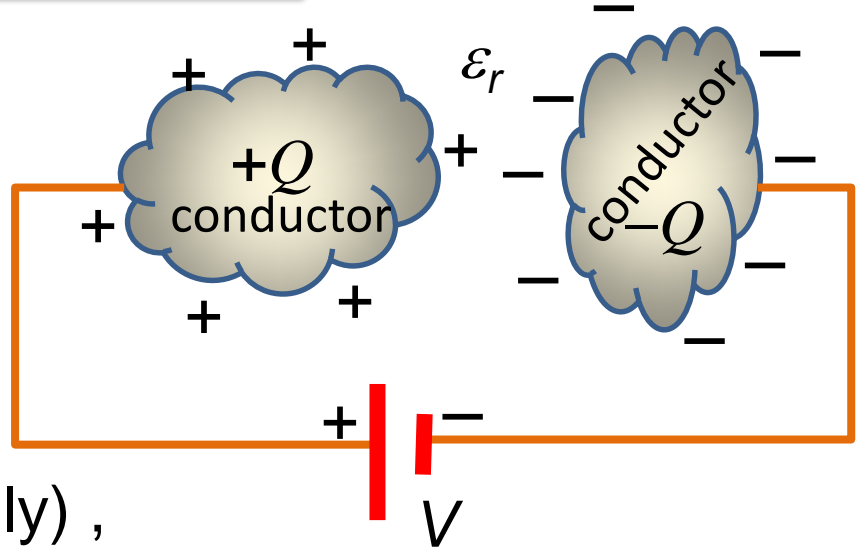
From previous calculations

$$V \propto Q,$$

define **capacitance** as

$$C \equiv \frac{Q}{V} \text{ (positive value only) ,}$$

which is the **stored charge per unit voltage**  
(a function of device **geometry** and relative **permittivity**  $\epsilon_r$ ).



# 7.1 電荷儲存

## Charge Storage

- Electric potential  $V$  is linearly proportional to the amount of charges  $q$  generating it.
- Connecting a battery (applying a voltage  $V$ ) to a pair of conductors (electrodes) stores charges into the system.
- Capacitance is the amount of stored charge per unit voltage, depending on the potential difference or voltage between electrodes, nearby material, and geometry of the system.

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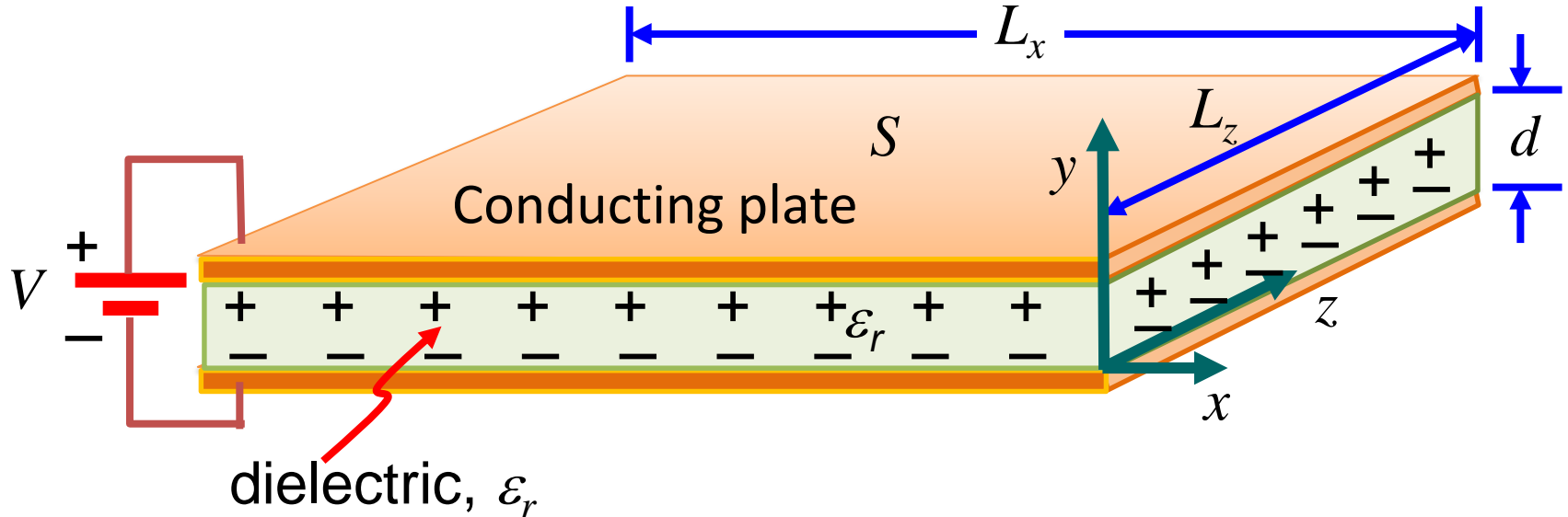
Capacitance

7.2 平板電容器

Parallel-plate Capacitor

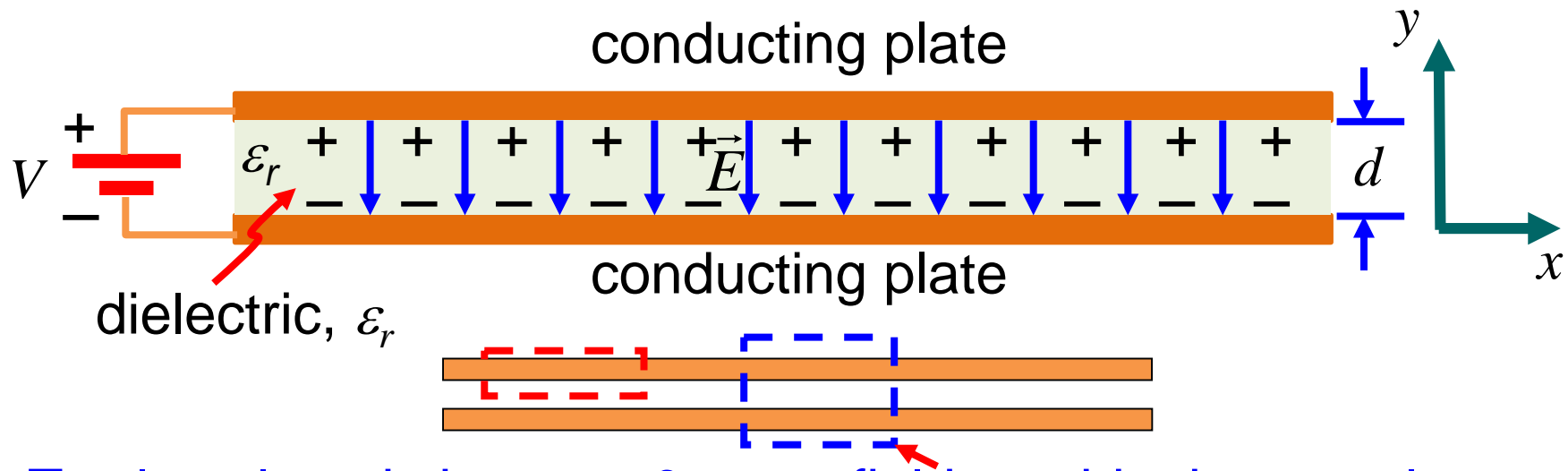


# Parallel-plate Capacitance



**Assumptions:**  $L_x, L_z \gg d$

$\Rightarrow$  fields are **more or less uniform** between plates  
(fringe fields are ignored during calculation)

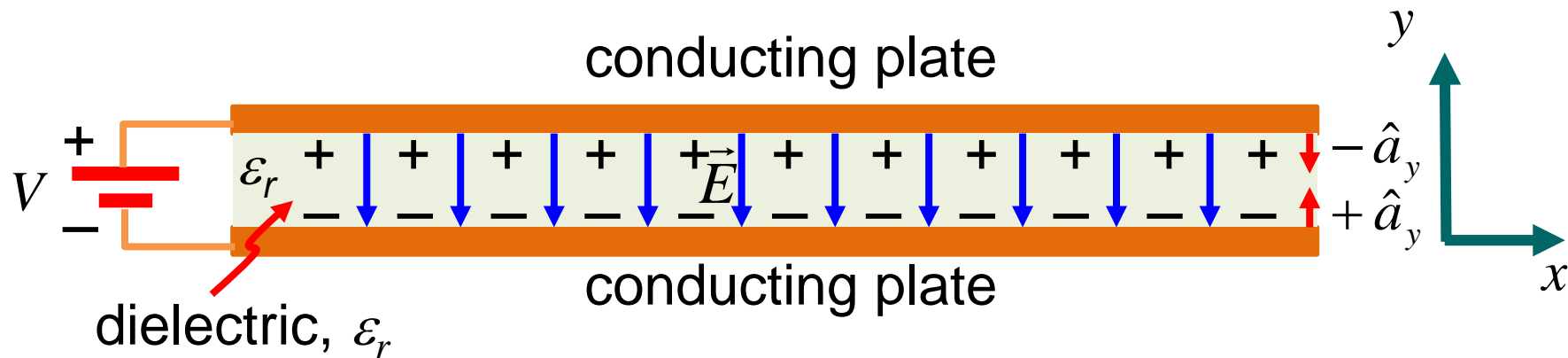


Total enclosed charge = 0  $\Rightarrow$  no field outside the two plates

Apply Gauss law to the surface defined by red dashed line

$$\epsilon \vec{E} \cdot \vec{S} = Q \Rightarrow (-\epsilon E_y \hat{a}_y) \cdot (-S \hat{a}_y) = Q \Rightarrow E_y = \frac{Q}{\epsilon S} = \frac{\rho_s}{\epsilon}$$

where  $S$  is the total area of the plate,  $\epsilon = \epsilon_0 \epsilon_r$  is permittivity of the dielectric, and  $Q$  is the total charge on  $S$ .



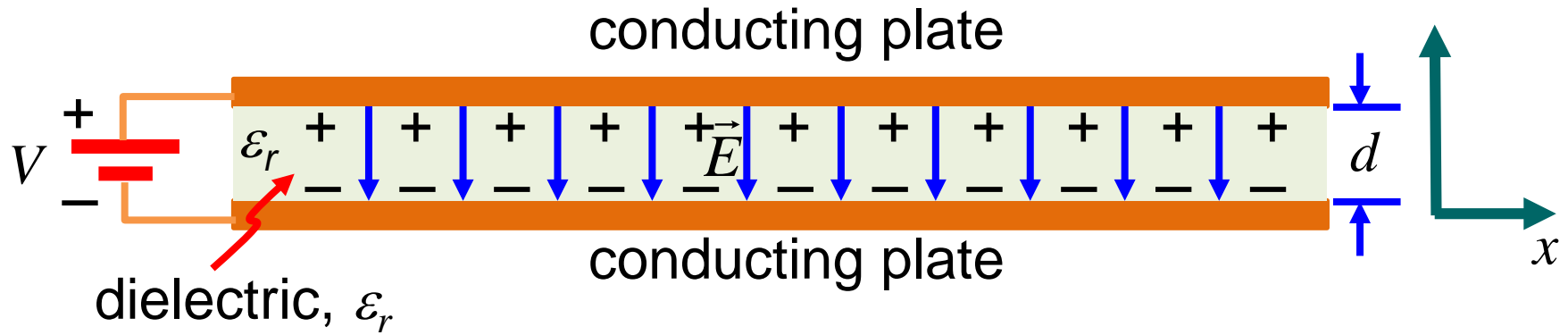
$$\vec{E} = -\frac{\rho_s}{\epsilon} \hat{a}_y \quad \longrightarrow \quad \vec{D} = \epsilon \vec{E} = -\rho_s \hat{a}_y$$

0 in conductor

Recall the B.C.  $\hat{a}_{n2} \cdot (\vec{D}_1 - \vec{D}_2) = \rho_s \quad \longrightarrow \quad \hat{a}_{n, \text{conductor}} \cdot \vec{D}_{\text{dielectric}} = \rho_s$

Upper conducting plate:  $-\hat{a}_y \cdot (-\rho_s \hat{a}_y) = \rho_s$

Lower conducting plate:  $\hat{a}_y \cdot (-\rho_s \hat{a}_y) = -\rho_s$



The voltage across the two electrodes is  $V = E_y d = \frac{dQ}{\epsilon S}$

The capacitance of this parallel plate capacitor is  $C \equiv \frac{Q}{V} = \frac{\epsilon S}{d}$

A large area  $S$ , a high permittivity  $\epsilon_r$ , and a small electrode gap  $d$  help to store charges under a voltage.

# Why does large $\epsilon_r$ give large $C$ ?

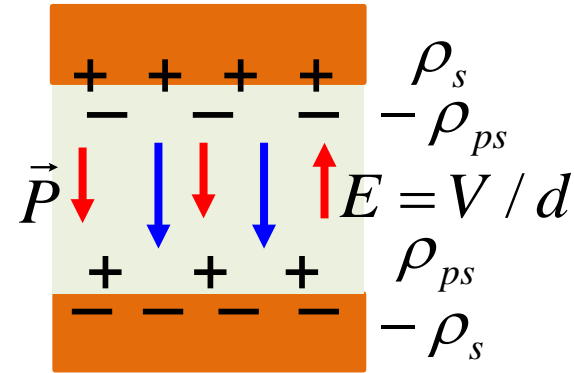
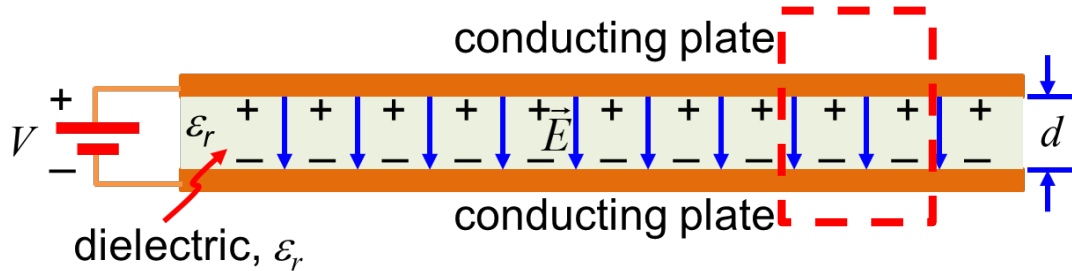
$E=V/d$  is fixed for a given  $V$ , but a large  $\epsilon_r$  results in a large  $D = \epsilon E$ .  $\rightarrow Q$  becomes larger due to  $D \propto \rho$  in  $\nabla \cdot \vec{D} = \rho$ .

Therefore,  $C = \frac{Q}{V}$  becomes larger when  $\epsilon_r \uparrow \rightarrow Q \uparrow$  for fixed  $V$ .

Physically, large  $\epsilon_r = 1 + \chi_e \rightarrow$  large  $\chi_e$ , but  $\vec{P} = \epsilon_0 \chi_e \vec{E}$ .

Recall  $\vec{P} \cdot \hat{a}_n = \rho_{ps} \rightarrow$  large  $P$  means large  $\rho_{ps}$

$\rightarrow$  large  $\rho_{ps}$  holds a large  $Q$  for a fixed  $V$ .



## 7.2 平板電容器

### Parallel-plate Capacitor

- Ignoring fringe fields, the capacitance of a parallel-plate capacitor is given by

$$C \equiv \frac{Q}{V} = \frac{\epsilon S}{d},$$

where  $S$  is the area of the electrode plate,  $d$  is the separation of the electrodes, and  $\epsilon$  is the permittivity of the dielectric between the electrodes.

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7.3 圓柱及球形電容

Cylindrical and Spherical Capacitors

## Cylindrical Capacitor (1)

Again, ignore the fringe fields at the edges.

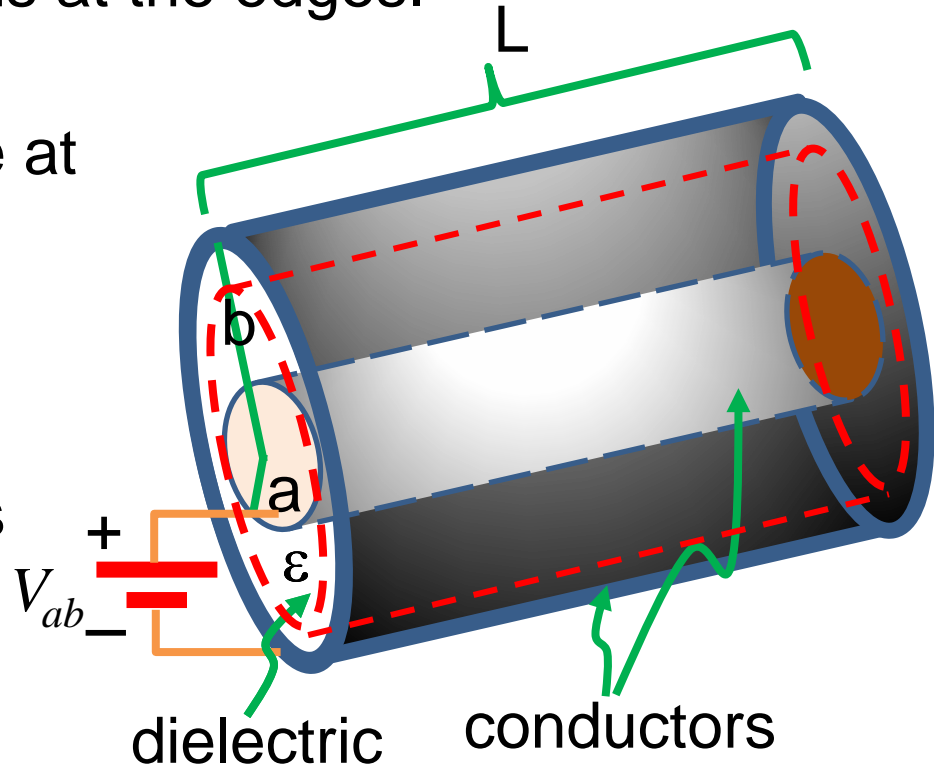
Apply Gauss's law to the cylindrical Gaussian surface at

a constant  $r$  
$$\epsilon \oint_S \vec{E} \cdot d\vec{s} = Q$$

➔ 
$$\hat{a}_r E_r = \hat{a}_r \frac{Q / \epsilon}{2\pi r L}$$

The electric potential across the two electrodes is

$$V_{ab} = - \int_{r=b}^{r=a} \vec{E}_r \cdot d\vec{r} = \frac{Q}{2\pi\epsilon L} \ln \frac{b}{a}$$





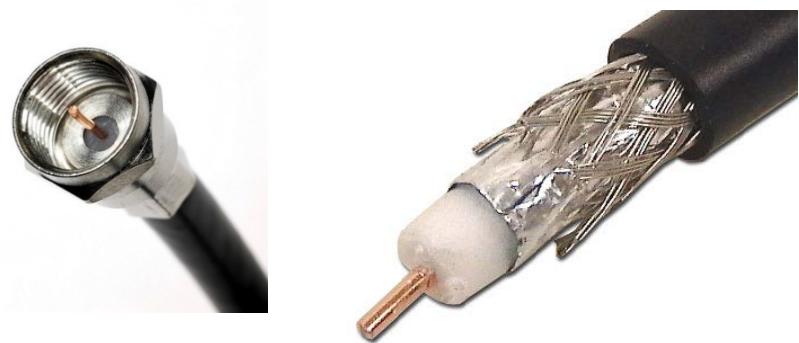
## Cylindrical Capacitor (2)

Take the ratio of  $Q$  and  $V$  to obtain the **capacitance** for a cylindrical capacitor

$$C \equiv \frac{Q}{V} = \frac{2\pi\epsilon L}{\ln(b/a)}$$

For a **transmission line**, what we care is the **capacitance per unit length**

$$C_l \equiv \frac{\rho_l}{V} = \frac{2\pi\epsilon}{\ln(b/a)}$$



Coaxial-cable transmission line

## Spherical Capacitor

Again, apply the **Gauss law** to the Gaussian

surface at a constant  $R \Rightarrow \epsilon \oint_S \vec{E} \cdot d\vec{s} = Q$

to obtain  $E_R = \frac{Q}{4\pi\epsilon R^2}$

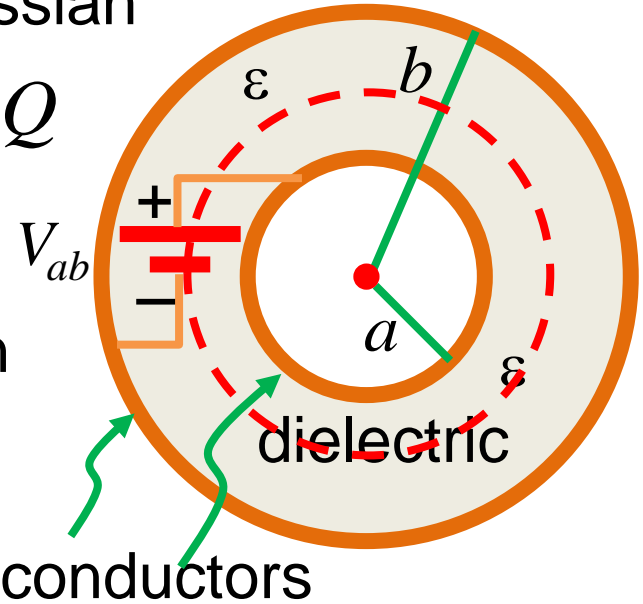
Calculate the **electric potential** between

$R = a$  and  $R = b$

$$V_{ab} = -\int_{R=b}^{R=a} \vec{E}_R \cdot d\vec{R} = \frac{Q}{4\pi\epsilon} \left( \frac{1}{a} - \frac{1}{b} \right)$$

Take the ratio of charge to voltage to obtain the **capacitance**

$$C \equiv \frac{Q}{V} = \frac{4\pi\epsilon}{(1/a - 1/b)}$$



## 7.3 圓柱及球形電容器

### Cylindrical and spherical capacitors

- A cylindrical capacitor consists of concentric electrodes filled with dielectric in between.
- The capacitance per unit length for a coaxial cable is given by

$$C_l = \frac{2\pi\epsilon}{\ln(b/a)}$$

- A spherical capacitor consists of two concentric spherical electrodes filled with dielectric in between.

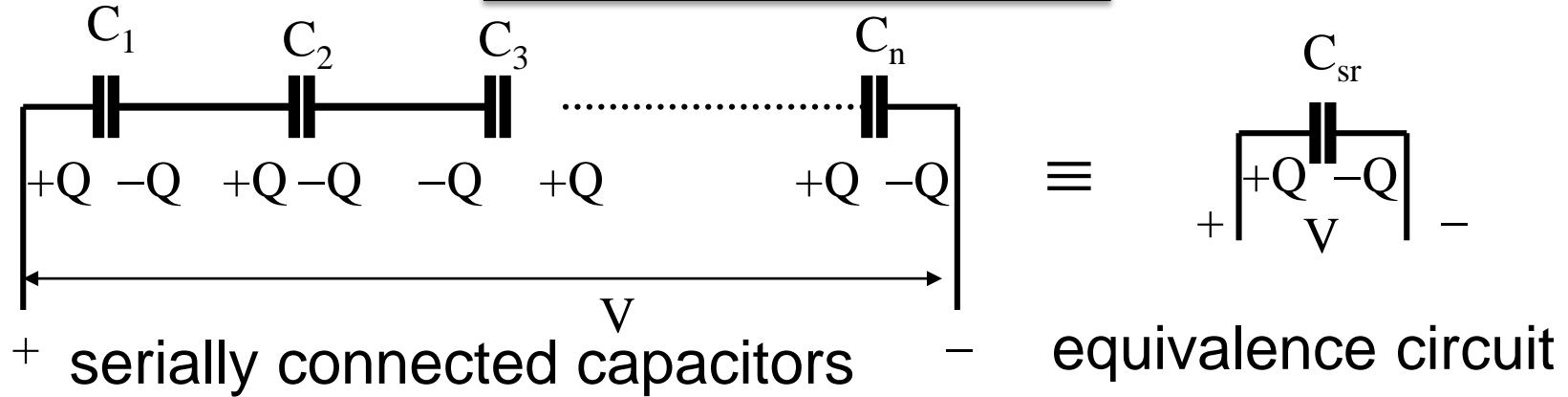
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Capacitance

7.4 電容電路

Capacitor Circuit

# Serial Capacitors



## Circuit expression

$$V = \frac{Q}{C_{sr}} = \sum_i V_i = \frac{Q}{C_1} + \frac{Q}{C_2} + \frac{Q}{C_3} \dots + \frac{Q}{C_n} \Rightarrow \frac{1}{C_{sr}} = \frac{1}{C_1} + \frac{1}{C_2} + \frac{1}{C_3} \dots + \frac{1}{C_n}$$

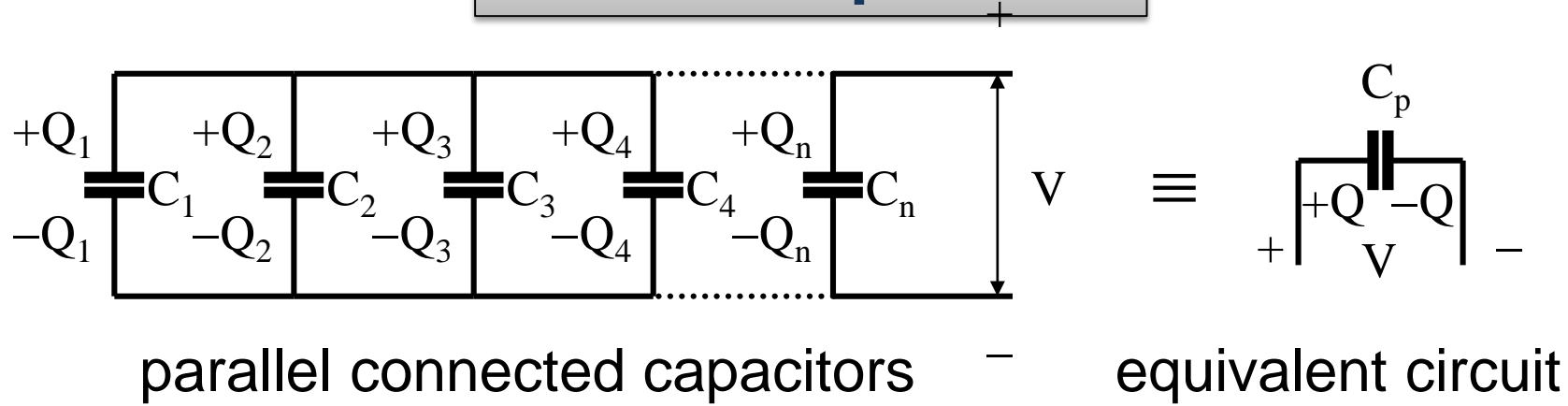
**Equivalent capacitance** – inverse of the inverse sum of  $C_i$

**Dominant term is the small  $C$  in**

$$C_{sr} = \left( \frac{1}{C_1} + \frac{1}{C_2} + \frac{1}{C_3} \dots + \frac{1}{C_n} \right)^{-1}$$

$$\frac{1}{C_1} + \frac{1}{C_2} + \frac{1}{C_3} \dots + \frac{1}{C_n}$$

# Parallel Capacitors



## Circuit expression

$$C_p V = Q = Q_1 + Q_2 + Q_3 + \dots + Q_n \quad \text{sum of individual capacitances}$$

$$= C_1 V + C_2 V + C_3 V + \dots + C_n V \quad \Rightarrow C_p = C_1 + C_2 + C_3 + \dots + C_n$$

Dominant term is the large  $C$  in  $C_1 + C_2 + C_3 + \dots + C_n$

The capacitance becomes larger as the areas for storing  $Q$  are added up.

## RC Discharging Circuit

capacitor discharging current  
= current entering the resistor

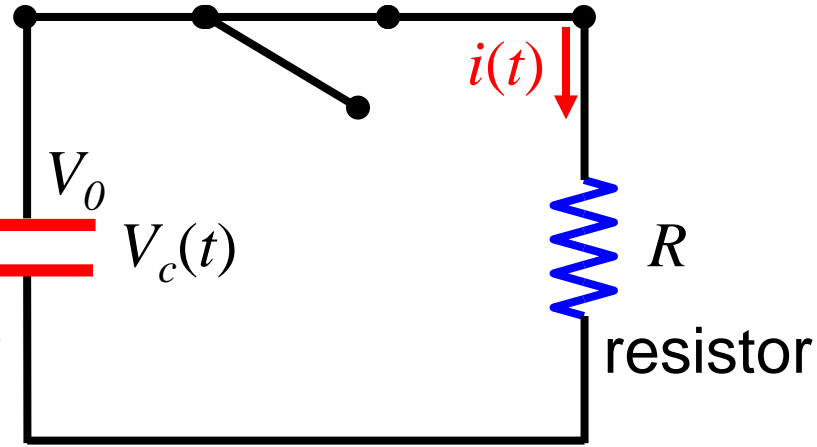
$$\frac{dQ_c}{dt} + \frac{V_c(t)}{R} = 0$$

Recall  $C = \frac{Q_c}{V_c}$

$$\Rightarrow C \frac{dV_c}{dt} + \frac{V_c(t)}{R} = 0$$

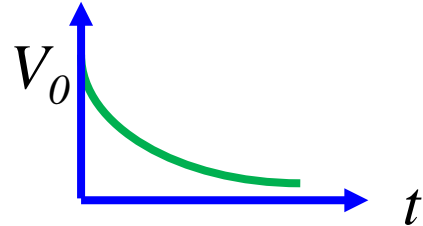
capacitor

$$Q_c(t) \quad \begin{array}{c} C \\ \hline V_0 \\ \hline V_c(t) \end{array}$$



$$\Rightarrow V_c(t) = V_0 e^{-t/RC} = V_0 e^{-t/\tau}$$

Capacitor voltage drops exponentially  
with a time constant  $\tau = RC$



## 7.4 電容電路

### Capacitor circuit

- The inverse of the equivalent capacitance of serial capacitors is the inverse sum of all the individual capacitances.

$$C_{sr} = \left( \frac{1}{C_1} + \frac{1}{C_2} + \frac{1}{C_3} \dots + \frac{1}{C_n} \right)^{-1}$$

- The equivalent capacitance of parallel capacitors is the sum of all the individual capacitances.

$$C_p = C_1 + C_2 + C_3 \dots + C_n$$

- An RC circuit charges/discharges with a time constant equal to

$$\tau = RC$$



# 電容

## Capacitance

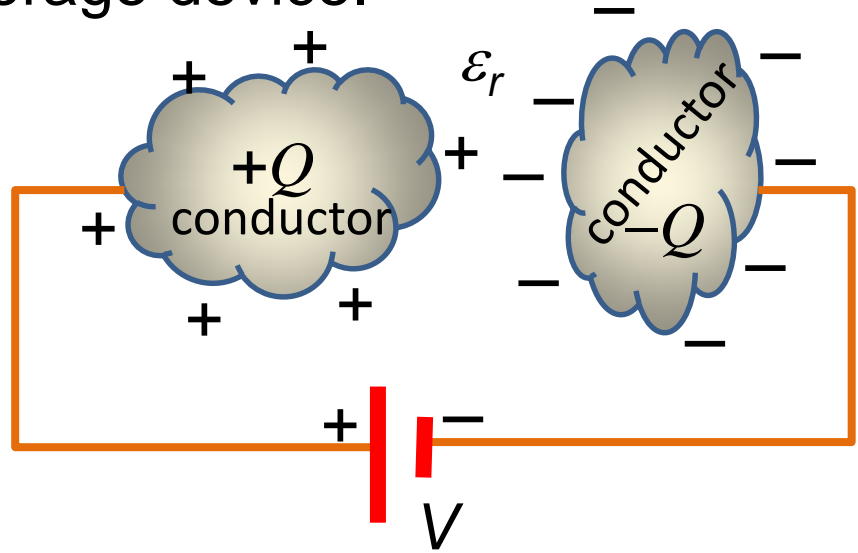
### 7.5 單元回顧 Review

# 單元回顧

1. A capacitor is a charge storage device.

2. Capacitance is defined as the amount of charges stored in a capacitor per unit voltage.

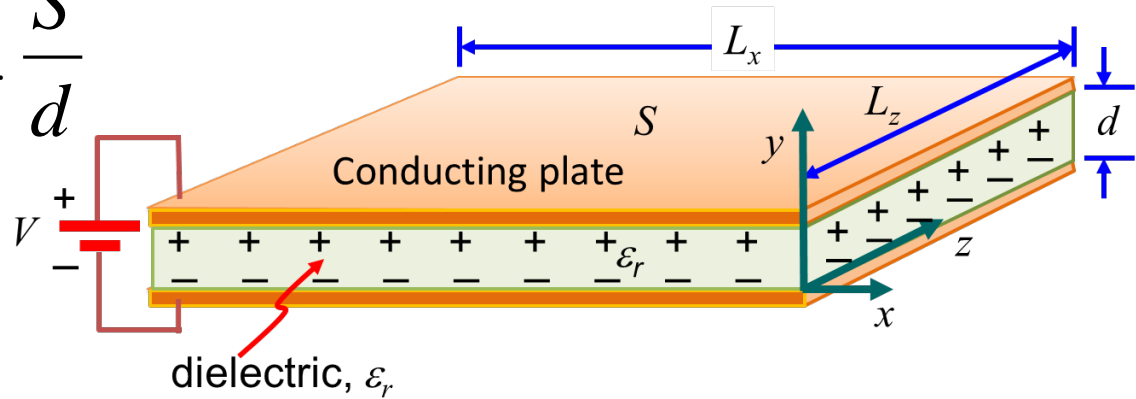
$$C \equiv \frac{Q}{V}$$



# 單元回顧

3. A parallel-plate capacitor has a capacitance of

$$C = \epsilon \frac{S}{d} = \epsilon_0 \epsilon_r \frac{S}{d}$$

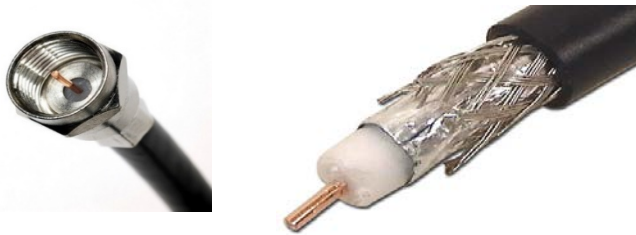


4. In general, a **large area  $S$** , a **high permittivity  $\epsilon_r$** , and a **small electrode gap  $d$**  give a high capacitance.

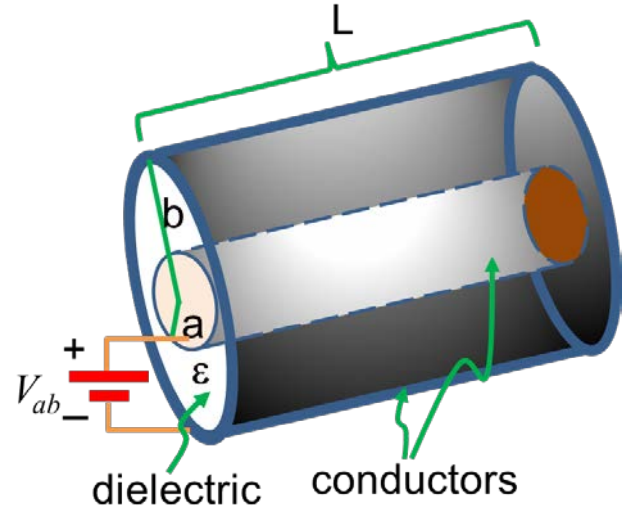
# 單元回顧

5. Calculation of a cylindrical capacitor leads to a formula for the capacitance per unit length of a coaxial cable

$$C_l \equiv \frac{\rho_l}{V} = \frac{2\pi\epsilon}{\ln(b/a)}$$



Coaxial-cable transmission line

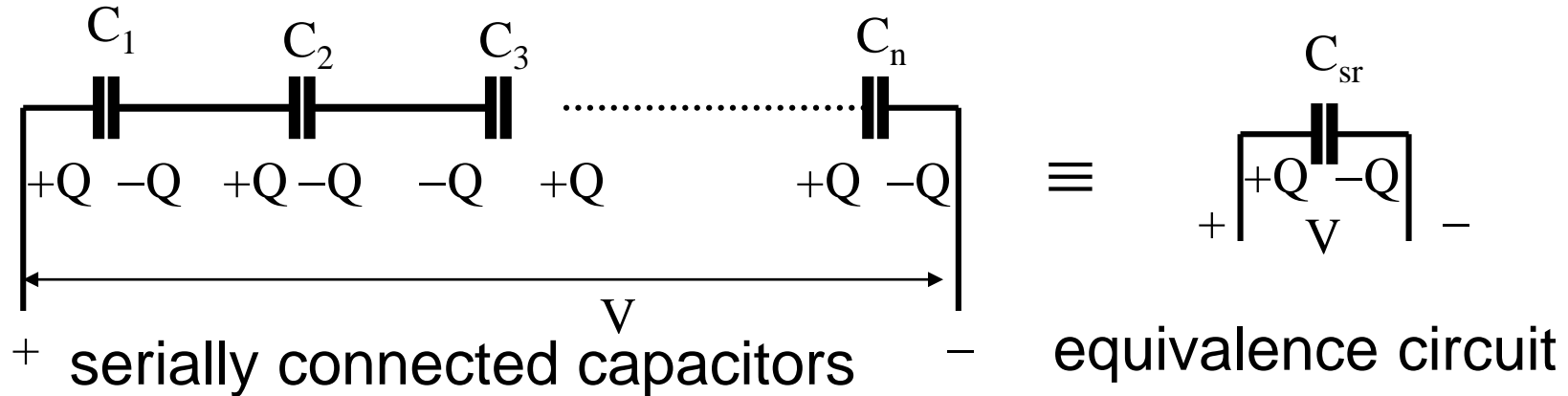


Cylindrical capacitor

# 單元回顧

6. The equivalent capacitance of serially connected capacitors is the inverse of the inverse sum of individual capacitances.

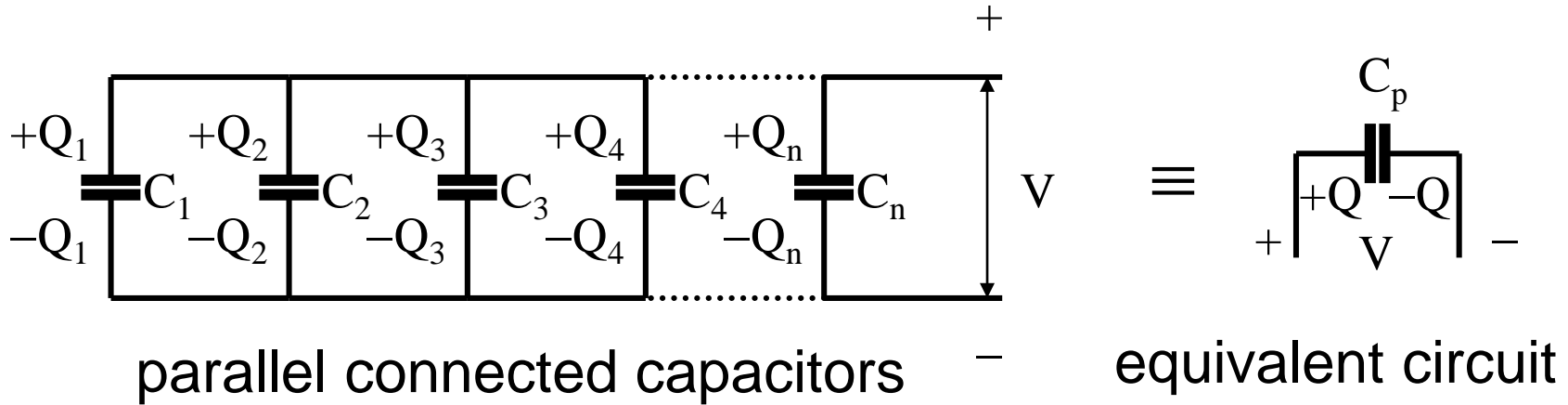
$$\frac{1}{C_{sr}} = \frac{1}{C_1} + \frac{1}{C_2} + \frac{1}{C_3} \dots + \frac{1}{C_n}$$



# 單元回顧

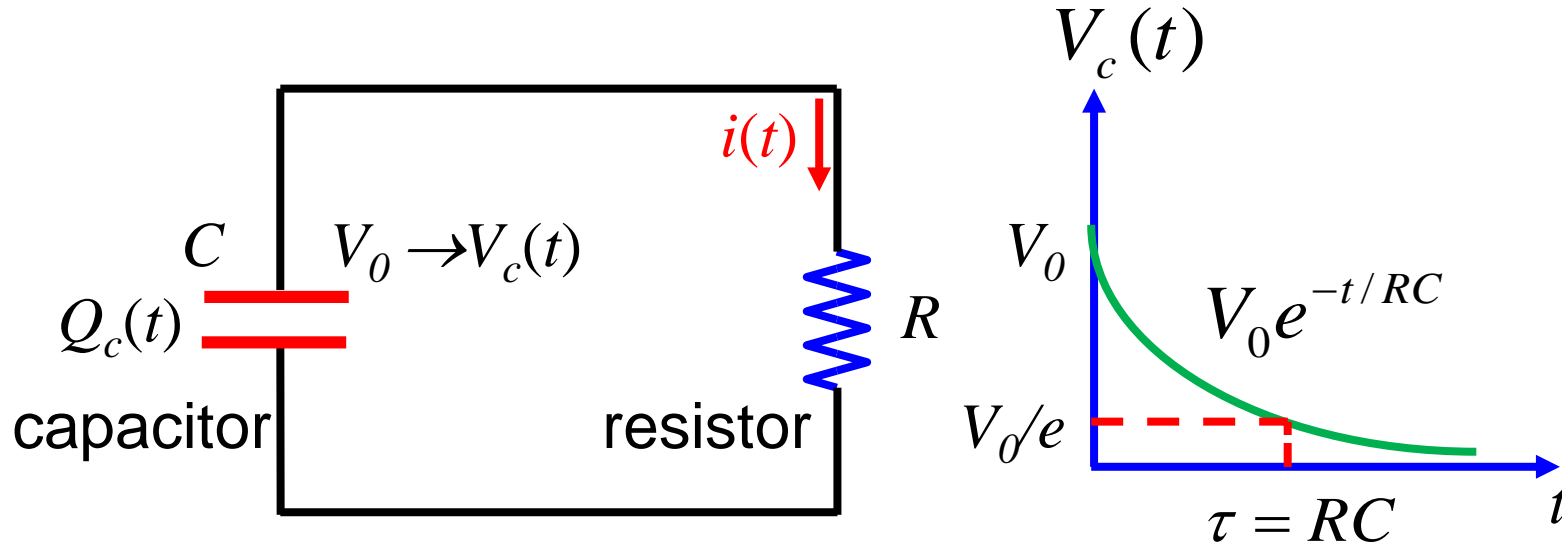
7. The equivalent capacitance of parallel connected capacitors is the sum of individual capacitances.

$$C_p = C_1 + C_2 + C_3 \dots + C_n$$



# 單元回顧

8. The characteristic charging/discharging time of an  $RC$  circuit is  $\tau = RC$ .



THANK YOU FOR YOUR ATTENTION

# Review Questions

1. When you design a capacitor, what are the key parameters to increase its capacitance?

Ans: From the formula of a parallel-plate capacitor,

$$C = \frac{\epsilon S}{d}$$

one could in general increase the capacitance of a capacitor by increasing the electrode areas and the permittivity of the dielectric between the electrodes, and decreasing the separation of the electrodes.



2. If you have a few capacitors in your hands and you want to connect them together to have a high capacitance for your circuit, would you choose serial or parallel connections for your capacitors?

Ans: To solve this problem, one could of course prove from the following two formulas for serial and parallel capacitors  $C_p > C_{sr}$

$$\frac{1}{C_{sr}} = \frac{1}{C_1} + \frac{1}{C_2} + \frac{1}{C_3} \dots + \frac{1}{C_n}$$

$$C_p = C_1 + C_2 + C_3 \dots + C_n.$$

However, from the circuit diagrams shown in Sec. 7.4, one can already see that the parallel capacitors store more charges from a increased area. Therefore, to increase the capacitance, parallel connection is the choice.

3. For a high-speed circuit containing R and C, if you would like to have a signal bandwidth  $> 1$  GHz, what is the requirement on the RC time constant of the circuit?

Ans: Consider a sinusoidal signal of 1 GHz in the circuit. Since the charging and discharging time in the circuit has to be less than  $1/1 \text{ GHz} \sim 1 \text{ ns}$  to support the 1 GHz signal, the RC time constant of the circuit has to be less than 1 ns.